

isc Silicon NPN Power Transistor

INCHANGE SEMICONDUCTOR

2SC2245

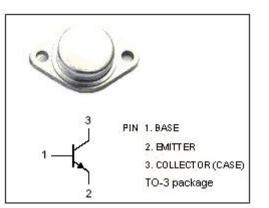
DESCRIPTION

- · High Collector-Emitter Sustaining Voltage-
- : V_{CEO(SUS)}= 400V (Min)
- High Switching Speed
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

APPLICATIONS

- Power switching
- Power amplification
- Power driver

ABSOLUTE MAXIMUM RATINGS(Ta=25°C) SYMBOL MAX UNIT PARAMETER V_{CBO} Collector-Base Voltage 450 V Collector-Emitter Voltage 400 VCEO V Emitter-Base Voltage 5 V_{EBO} V Collector Current-Continuous 10 А lc Collector Current-Peak Ісм 20 А **Base Current-Continuous** 4 А I_{B} **Collector Power Dissipation** Pc 100 W @Tc=25°C Tj 200 °C Junction Temperature



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DIM A B		
A B	39.	00
A	39. 25.30	00 26.67
A B C	39. 25.30 7.80	00 26.67 8.50
A B C D	39. 25.30 7.80 0.90	00 26.67 8.50 1.10 1.60
A B C D E	39 25.30 7.80 0.90 1.40 10	00 26.67 8.50 1.10 1.60
A B C D E G	39 25.30 7.80 0.90 1.40 10	00 26.67 8.50 1.10 1.60 92
A B C D E G H	39. 25.30 7.80 0.90 1.40 10. 5	00 26.67 8.50 1.10 1.60 92 46
A B C D E G H K	39 25.30 7.80 0.90 1.40 10 5 11.30	00 26.67 8.50 1.10 1.60 92 46 13.50 17.05 19.62
A B C D E G H K L	39 25.30 7.80 0.90 1.40 10. 5 11.30 16.75	00 26.67 8.50 1.10 1.60 92 46 13.50 17.05 19.62
A B C D E G H K L N	39 25.30 7.80 0.90 1.40 10 5 11.30 16.75 19.40	00 26.67 8.50 1.10 1.60 92 46 13.50 17.05

	CHARACTERISTICS
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T_{stg}

SYMBOL	PARAMETER	МАХ	UNIT
R _{th j-c}	Thermal Resistance, Junction to Case	1.0	°C/W

-65~200

1

°C

Storage Temperature Range

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ELECTRICAL CHARACTERISTICS

$T_c=25^{\circ}C$ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _{CEO(SUS)}	Collector-Emitter Sustainig Voltage	I _C = 50mA; L= 25mH	400			V
V _{CE(sat)}	Collector-Emitter Saturation Voltage	I _C = 4A; I _B = 0.8A			1.2	V
V _{BE(sat)}	Base-Emitter Saturation Voltage	I _C = 4A; I _B = 0.8A			1.5	V
h _{FE}	DC Current Gain	I _C = 4A; V _{CE} = 5V	10			
I _{CBO}	Collector Cutoff Current	V _{CB} = 450V; I _E = 0 T _C =125℃			1.0 4.0	mA
I _{CEO}	Collector Cutoff Current	V _{CE} = 400V; I _B = 0			5.0	mA
Іево	Emitter Cutoff Current	V _{EB} = 5V; I _C = 0			1.0	mA

Switching Times

tr	Rise Time	I _C =4A; I _{B1} =- I _{B2} = 0.8A		1.0	μ s
t _{stg}	Storage Time			2.0	μ S
t _f	Fall Time			1.0	μ S

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